

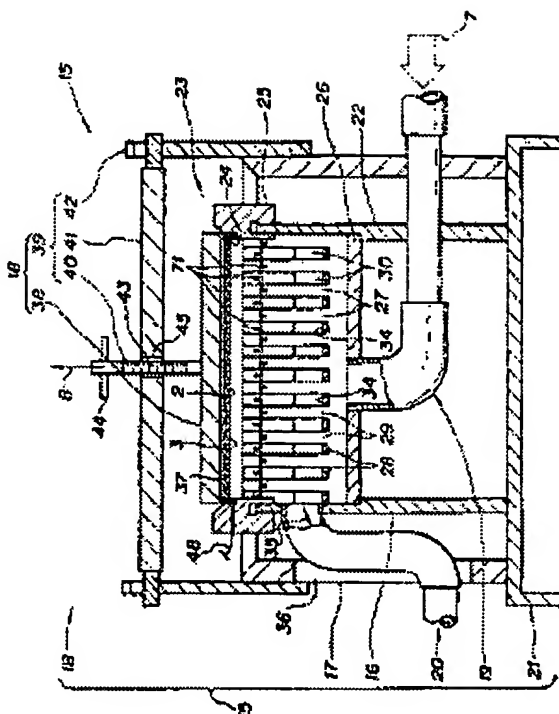
## METHOD FOR PLATING SEMICONDUCTOR WAFER

**Patent number:** JP62297495  
**Publication date:** 1987-12-24  
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**Classification:**  
 - international: C25D7/12; H01L21/288  
 - european:  
**Application number:** JP19860139315 19860617  
**Priority number(s):**

### Abstract of JP62297495

**PURPOSE:** To easily form a high quality metallic plating layer on the surface of a semiconductor wafer by plating by jetting many jets of a plating soln. on the surface of the wafer from one of first and second groups of nozzles and recovering the plating soln. through the other.

**CONSTITUTION:** A manual wheel 44 is rotated to move a pressing body 38 upward, a semiconductor wafer 2 having a formed resist layer is set on a sealing part 24 the wheel 44 is reversely rotated to fix the wafer 2 with the pressing body 38. A plating soln. 7 is fed from a first pipe 19 to a first group of nozzles 29 through the openings 27 of a second groups of lower receiving members 28 and many jets of the plating soln. are jetted on the surface of the wafer 2 to form a layer of the plating soln. The plating soln. 35 jetted from the nozzles 29 flows down into a second group of nozzles 30 and flows along the surfaces 34 of the receiving members 28. The soln. is then discharged from a second pipe 20 and recovered.



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